**Product data sheet** 

## 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring enhanced immunity to noise and direct interfacing to logic level ICs and low power gate drivers.

### 2. Features and benefits

- · Direct interfacing to logic level ICs
- Enhanced current surge capability
- · Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Surface-mountable package
- Triggering in all four quadrants

## 3. Applications

- General purpose low power motor control
- · Home appliances
- Industrial process control
- Low power AC Fan controllers

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage			-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3		-	-	1	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5		-	-	12.5	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$		-	-	13.8	Α
T <sub>j</sub>	junction temperature			-	-	125	°C
Static characteristics							
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$		0.4	-	10	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	0.4	-	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
Dynamic char	acteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 14	120	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 ^{\circ}\text{C}; dl_{com}/$ dt = 0.44 A/ms; gate open circuit	2	-	-	V/µs

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2—T1
2	T2	main terminal 2		G sym051
3	G	gate		Symost
4	T2	main terminal 2	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
Z0109NN0	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

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# 7. Limiting values

## **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	1	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5	-	12.5	А
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms	-	13.8	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.78	A²s
dl <sub>T</sub> /dt	rate of rise of on-state	I <sub>G</sub> = 20 mA; T2+ G+	-	50	A/µs
	current	I <sub>G</sub> = 20 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G+	-	20	A/µs
I <sub>GM</sub>	peak gate current		-	1	Α
$P_{GM}$	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

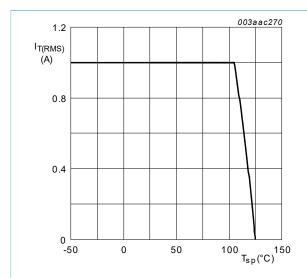


Fig. 1. RMS on-state current as a function of solder point temperature; maximum values

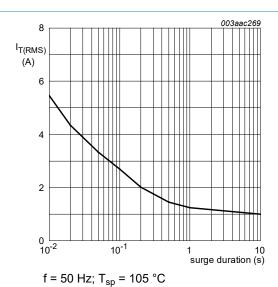


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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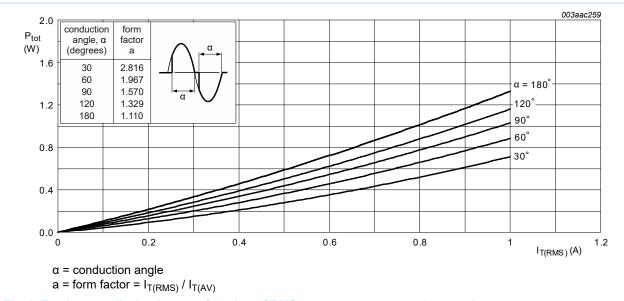


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

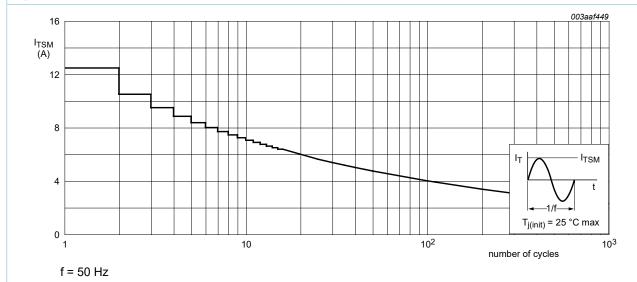
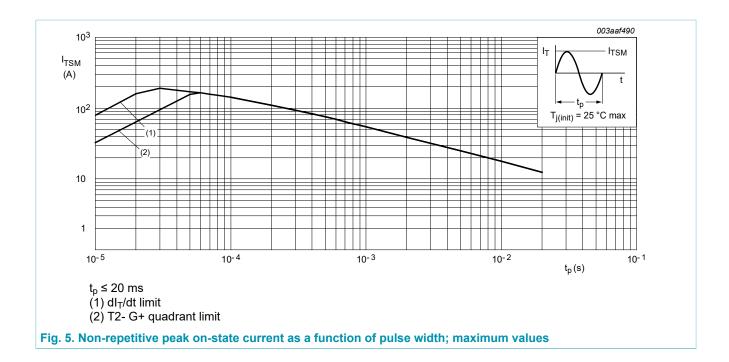


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air; printed-circuit board mounted: minimum footprint; full cycle; Fig. 7	-	156	-	K/W
		in free air; printed-circuit board mounted: pad area; full cycle; Fig. 8	-	70	-	K/W

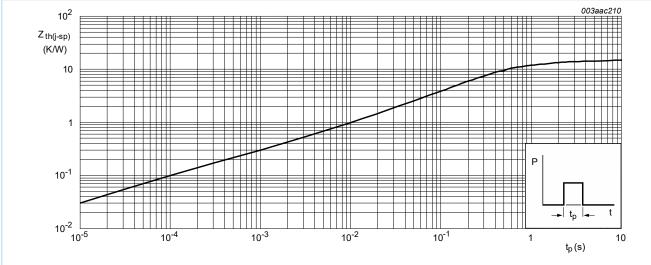
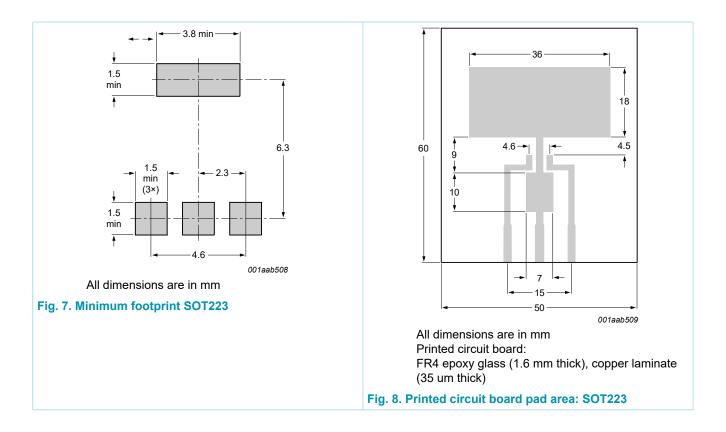


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width

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## 9. Characteristics

#### Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			,
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	0.4	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 9$	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 9}}$	0.4	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;} $ $T_j = 25 \text{ °C; } Fig. 9$	0.4	-	10	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 10}$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 10}$	-	-	15	mA
Н	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	-	10	mA
√ <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
√ <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 13	-	-	1	V
		V <sub>D</sub> = 800 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 13	0.2	-	-	V
D	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
Dynamic ch	naracteristics		'	'		_
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 14	120	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	V <sub>D</sub> = 400 V; T <sub>j</sub> = 110 °C; dl <sub>com</sub> / dt = 0.44 A/ms; gate open circuit	2	-	-	V/µs

3

2

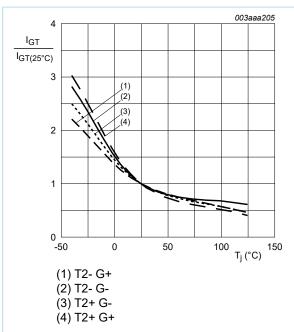
0

-50

I<sub>L(25°C)</sub>

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003aaa203



T<sub>i</sub> (°C) Fig. 10. Normalized latching current as a function of junction temperature

50

100

150

0



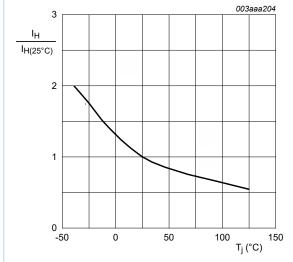
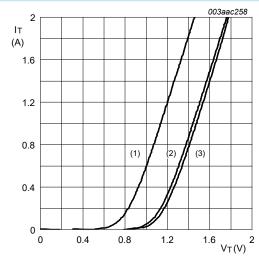


Fig. 11. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$  $R_s = 0.31 \Omega$ 

(1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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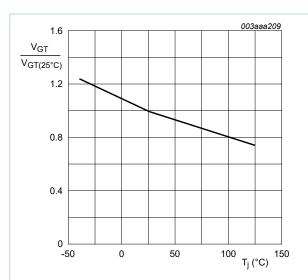


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

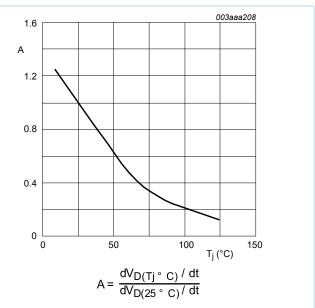


Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

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## 10. Package outline

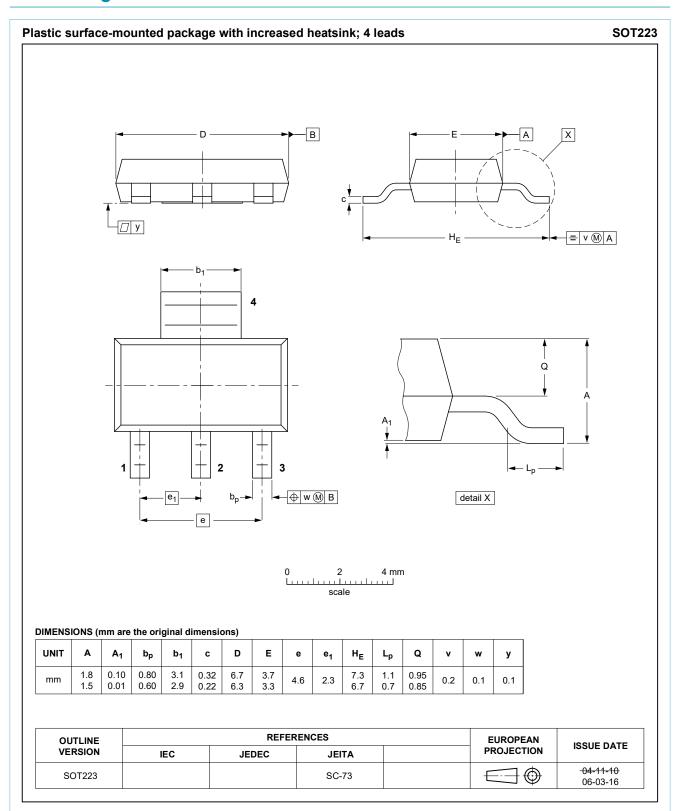


Fig. 15. Package outline SC-73 (SOT223)

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## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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For more information, please visit: http://www.ween-semi.com
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